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## **Thiol-functionalization of Mn<sub>5</sub>Ge<sub>3</sub> thin films**

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### **HIGHLIGHTS**

The surface state of Mn<sub>5</sub>Ge<sub>3</sub> exposed to air and common solvents, is analyzed by XPS.

The surface free energy of Mn<sub>5</sub>Ge<sub>3</sub> is calculated with the OWRK method.

The grafting of Mn<sub>5</sub>Ge<sub>3</sub> films by octane- and perfluorodecane-thiol SAMs is proposed.

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### **KEYWORDS**

thiol; passivation; self-assembled monolayers; manganese germanide; Mn<sub>5</sub>Ge<sub>3</sub>; wettability; spintronics; surface free energy.

## 25 ABSTRACT

Hybrid organic/inorganic interfaces could pave the way to chemically designed or new multifunctional electronic devices, in particular in the spintronics field where, for instance, the interfacial spin polarization can be tuned through chemical interactions and surface modifications. We report herein, for the very first time, the assays of self-assembled monolayers (SAMs) formation on  $\text{Mn}_5\text{Ge}_3$  surface. Interestingly,  $\text{Mn}_5\text{Ge}_3$  is a ferromagnetic metal possessing interesting features for spintronics such as a high Curie temperature, a capability to grow epitaxially on Ge germanium that is a key point for integration in the mainstream Si technology.  $\text{Mn}_5\text{Ge}_3$  thin films are synthesized by molecular beam epitaxy under ultra-vacuum condition. We studied the  $\text{Mn}_5\text{Ge}_3$  surface prior to deposition of SAMs, meaning the surface exposed to air and different solvents, by XPS and contact angle measurements leading to the value of the surface tension of this surface. Then SAMs of octanethiol and perfluorodecanethiol are formed on  $\text{Mn}_5\text{Ge}_3$  surface at room temperature. The best experimental conditions to form the SAMs are found for an immersion time of 36 h and a concentration of 4 mM.

## 1 INTRODUCTION

Over the last decade the manganese germanide  $\text{Mn}_5\text{Ge}_3$  has appeared to be a potential candidate for spin injection into group-IV semiconductors due to its room-temperature ferromagnetism properties (Curie temperature  $T_C = 297$  K), high spin polarization, metallic character, ability to epitaxially grow on Ge(111) substrates as well as compatibility with the already-existing Si-Ge-based technology [1–3]. Moreover, several studies have shown that its  $T_C$  can be enhanced by carbon doping into the interstitial sites of the  $\text{Mn}_5\text{Ge}_3$  lattice and that the Schottky contact between Ge and  $\text{Mn}_5\text{Ge}_3$  may be suitable for electrical spin injection [4–7]. Furthermore, hybrid structures of organic molecules and inorganic materials have been recently in the spintronic community's crossroad. The first purpose was to use the molecules as spin transport media because of the rather weak coupling between the spin and orbital momentum of the electron that allows keeping the spin orientation over long distances. It has been rapidly anticipated that molecules could also have strong impacts on the magnetic properties, for instance, several teams dealing with spin valves reported negative magnetoresistance [8,9]. These phenomena confirmed the growing interest on the developing molecular “spinterface” which could lead to single multi-functional devices thanks to the “LEGO” capability of molecular engineering [10–13]. Molecules and biomolecules possessing a magnetic core are potential candidates to be grafted on the magnetic substrate  $\text{Mn}_5\text{Ge}_3$ . One of the most promising approaches to modify surface involves the

deposition of organic self-assembled monolayers (SAMs). SAMs constitute a method of choice to achieve highly dense and ordered thin films, robustly anchored to large surface areas either on clean metallic (e.g. Au, Ag), oxidized (e.g. SiO<sub>2</sub>, ITO) or semiconducting (e.g. Si, Ge) substrates. This method does not require either sophisticated and expensive instrumentation, or intricate sample  
60 preparations, expert manpower and allows the opportunity to vary both the length of the chains and functional groups to manipulate macroscopic properties of the surface, such as wettability, biocompatibility and protein/cellular adhesion [14–17]. Furthermore, magnetic properties of metals and diluted magnetic semiconductors (DMS) such as (Ga, Mn)As have been tailored by SAMs surface modifications leading to induced magnetic moments or modification of ferromagnetic properties [18–  
65 20].

Alkanethiols are so far the most studied self-assembled molecules because of the covalent polarized bond formed between thiol headgroups and appropriate substrates (e.g. Au, Ge, Ag, Cu, Pt, Hg, GaAs). Regarding Ge surface, HBr and HCl are often used to halogenate the surface of this semiconductor prior to the SAMs formation, mainly to avoid the process of reoxidation of the surface. Indeed, the  
70 classical hydrogenation, which is used for silicon surface passivation, is less stable in the case of the Ge surface [21–25]. The inherent ability of adsorbed monolayers to modify physicochemical properties of surfaces makes this approach attractive to implement the organic functionalization of the surface of the Mn<sub>5</sub>Ge<sub>3</sub>/Ge system. To the best of our knowledge, functionalization of Mn<sub>5</sub>Ge<sub>3</sub>/Ge with alkylthiols has never been done before. The Mn<sub>5</sub>Ge<sub>3</sub> thin films being elaborated under ultra high vacuum conditions by  
75 molecular beam epitaxy (MBE), we present herein a study of the surface state of the Mn<sub>5</sub>Ge<sub>3</sub> thin films under air and common solvents exposure and secondly the first insights on the functionalization of Mn<sub>5</sub>Ge<sub>3</sub> with thiol molecules.

## 2 MATERIALS AND METHODS

### 80 2.1 Substrates.

Sb-doped Ge(111) wafers (n-type, 600 μm thickness, 12-16 Ω cm) were purchased from Umicore (Belgium). Mn<sub>5</sub>Ge<sub>3</sub>/Ge(111) heterostructures were grown by molecular beam epitaxy (MBE) technique according to the method described by Petit & *al* [26]. This method is based on the co-deposition at room temperature of Mn and Ge. It allows growing high crystalline quality films of Mn<sub>5</sub>Ge<sub>3</sub> with an

85 abrupt interface on Ge(111) and with a small RMS roughness (ca. 2 nm). The Mn<sub>5</sub>Ge<sub>3</sub> thin films were 30 nm thick.

## 2.2 Grafting procedures.

2.2.1 **Cleaning.** Mn<sub>5</sub>Ge<sub>3</sub>/Ge(111) substrates were first successively sonicated in acetone, deionized water and ethanol. Each cleaning step was repeated three times with a fresh solvent for 5 min, followed  
90 by blow-drying with argon gas.

2.2.2 **Thiol-functionalization.** Cleaned Mn<sub>5</sub>Ge<sub>3</sub>/Ge(111) substrates were immersed into octanethiol (OT) (CH<sub>3</sub>(CH<sub>2</sub>)<sub>7</sub>SH, Alfa Aesar) or perfluorodecanethiol (PFDT) (CF<sub>3</sub>(CF<sub>2</sub>)<sub>7</sub>CH<sub>2</sub>CH<sub>2</sub>SH, Sigma-Aldrich) solutions for surface functionalization. The experiments were carried out at room temperature to avoid any interdiffusion of Ge and Mn at the Mn<sub>5</sub>Ge<sub>3</sub>/Ge interface that could be detrimental for  
95 further spintronic applications. Freshly thiol solutions were prepared in ethanol prior to be used. The vials were backfilled with argon gas in order to minimize O<sub>2</sub> in the headspace. After experiments, the substrates were rinsed three times with ethanol to remove physisorbed molecules on the surface and dried over 24 h in a desiccator at room temperature. We have mainly investigated two parameters: i) the thiol concentration (from 1 to 5 mM) and ii) the immersion reaction time (from 12 to 24, 36, 48 and  
100 72 h). First, a range of concentration of thiol was tested, at fixed immersion time of 24h, in order to determine the optimal concentration needed. Optimum condition of concentration was selected (4 mM, see the Results and Discussion) and experiments were conducted by varying the immersion times.

## 2.3 Characterizations.

Foremost, a chemical analysis of the untreated Mn<sub>5</sub>Ge<sub>3</sub> substrates have been done by X-ray  
105 photoelectrons spectroscopy (XPS) in an ultrahigh vacuum system equipped with an Omicron DAR 400 X-ray source. The Mg anode was used to perform the analysis. The hemispherical analyser (HSA) is an Omicron EA 125 (normal detection was used). The angle between the X-ray source and the HSA was equal to 55°. The topographies of the substrates were imaged by atomic force microscopy (AFM) with a Nanoscope IIIA Multimode (Digital instruments) equipped with a 10×10×2.5 μm scanner. The  
110 images were recorded in the tapping mode at room temperature using silicon nitride probes (HQ: NSC15/AL BS, Mikromasch). The curvature radius of the silicon tips was about 8 nm (from the supplier specifications). Contact angle measurements were performed for the assessment of the hydrophobic-hydrophilic character of the substrates. Static contact angles (CA) were measured with an OCA 15 apparatus (DataPhysics) at room temperature using the sessile drop method and image

115 analysis of the drop profile (SCA20 software). Deionized water droplet volume was 5  $\mu\text{L}$ , and the contact angle was measured 10 s after the drop was deposited onto the surface.

### 3 RESULTS AND DISCUSSION

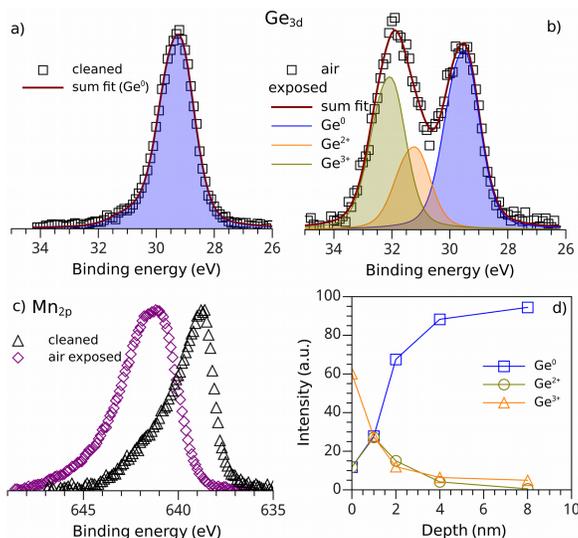
#### 3.1 Characterization of the $\text{Mn}_5\text{Ge}_3/\text{Ge}(111)$ substrates before the grafting process.

120 **3.1.1 XPS:** The  $\text{Mn}_5\text{Ge}_3$  samples were grown in a MBE chamber and taken out from the UHV chamber for the grafting process. The different samples were exposed successively to atmosphere and chemical cleaning prior undergoing the SAMs grafting procedures. To our knowledge this is the first report describing both aging changes of the  $\text{Mn}_5\text{Ge}_3$  surface under air exposure, stability under chemical cleaning/etching with polar aprotic or protic solvents such as acetone and ethanol respectively.

125 After air exposure,  $\text{Mn}_5\text{Ge}_3$  surface has been analyzed by XPS in order to determine the chemical state of the surface atoms and then the surface free energy has been measured. The  $\text{Ge}_{3d}$ ,  $\text{O}_{1s}$  and  $\text{Mn}_{2p}$  core levels were recorded and the parameters for the XPS fits are given in the electronic supplementary information (ESI). The Figure 1 shows the electronic state of the  $\text{Mn}_5\text{Ge}_3$  surface after air exposure. Figures 1a and 1b exhibit the evolution of the  $\text{Ge}_{3d}$  core level before (cleaned) and after air exposure  
130 whereas fig. 1c concerns the evolution of the  $\text{Mn}_{2p}$  core level. The “cleaned”  $\text{Ge}_{3d}$  core level exhibits one peak at 29.1 eV, related to Ge atoms in the bulk state in  $\text{Mn}_5\text{Ge}_3$  (blue contributions in Figure 1a and 1b respectively). On Fig.1b, the peak around 31.5 eV is typical of germanium oxide. It can be deconvoluted into two main contributions corresponding to the Ge atoms in the oxidized states  $\text{Ge}^{2+}$  and  $\text{Ge}^{3+}$  [27]. Thus, the oxidized state of the Ge atoms differs from a cleaned (non oxidized)  $\text{Mn}_5\text{Ge}_3$   
135 surface and to a  $\text{Ge}(111)$  substrate in which the  $\text{Ge}^{4+}$  state, corresponding to the  $\text{GeO}_2$  oxide (see ESI), is prevailing. This difference is also confirmed by the analysis of the  $\text{O}_{1s}$  core levels (see ESI). Regarding the  $\text{Mn}_{2p}$  core level (Fig. 1c), the oxidation by air leads to a strong shift of about 2.5 eV at higher energy that could be attributed to the Mn atoms in oxidized states around 2-2.7<sup>+</sup> similar to those found in  $\text{MnO}$  or  $\text{Mn}_3\text{O}_4$  [28]. These features confirm a clear difference for the native oxide structures  
140 of  $\text{Ge}(111)$  and  $\text{Mn}_5\text{Ge}_3$  suggesting that the latter may correspond to a ternary oxide of Mn-Ge-O.

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155 **Figure 1:** XPS spectra related to the effect of air exposure on the Mn<sub>5</sub>Ge<sub>3</sub> surfaces. a) Reference: Ge<sub>3d</sub> core level of a cleaned (non oxidized) Ge(111) substrate. b) Deconvolution of the Ge<sub>3d</sub> core levels from an oxidized Mn<sub>5</sub>Ge<sub>3</sub> surfaces. c) Superposition of Mn<sub>2p<sub>3/2</sub></sub> core levels of a cleaned and oxidized Mn<sub>5</sub>Ge<sub>3</sub> layers. d) Evolution of the contributions of the Ge<sub>3d</sub> core level according to a depth profile of oxidized Mn<sub>5</sub>Ge<sub>3</sub> thin films done by ionic Ar<sup>+</sup> bombardment.

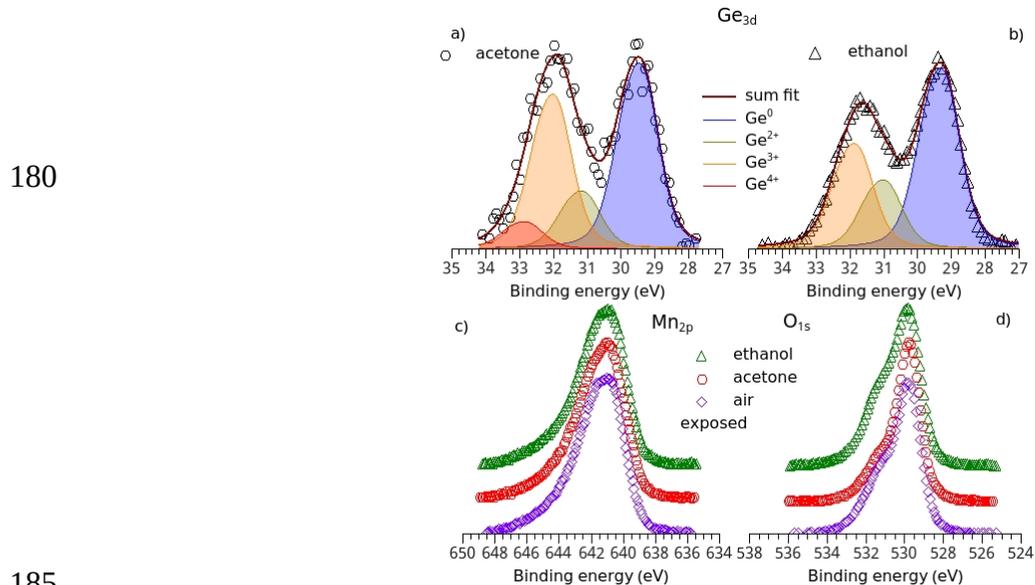
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Moreover the Fig. 1d exhibits the evolution of the Ge<sup>0</sup> as well as the oxide contributions Ge<sup>2+</sup> and Ge<sup>3+</sup> for the Ge<sub>3d</sub> core level along a depth profile in the oxidized Mn<sub>5</sub>Ge<sub>3</sub> layer. The depth profile has been made using an Ar<sup>+</sup> ionic sputtering. We have evidenced that the oxidation of the Mn<sub>5</sub>Ge<sub>3</sub> thin film took place in the first 4 nm, after one week of air exposure. This indicates that the oxidation of the Mn<sub>5</sub>Ge<sub>3</sub> film is not limited to the very surface and oxygen diffuses into the layer. Prior the SAMs formation, the Mn<sub>5</sub>Ge<sub>3</sub> film surface is successively cleaned with acetone then ethanol and carefully analysed each step by XPS (Figure 2). The Ge<sub>3d</sub> core level is followed after each solvent rinse highlighting specific behaviours (Fig. 2a, 2b). For instance, after acetone cleaning, the surface exhibits a Ge<sup>4+</sup> contribution unlike the ethanol case. The deconvolution profile after ethanol treatment is very similar to the one of the air exposed sample and also the intensity of the overall oxide component is smaller than in that

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case. This last observation could be explained by the fact that  $\text{GeO}_2$  is soluble in water and that we used a 96% ethanol. This is consistent with several studies regarding the influence of wet surface treatments and SAM deposition processes which have demonstrated that water or a mixture of water and ethanol can dissolve germanium oxide [24,29,30]. Surprisingly, concerning the  $\text{Mn}_{2p_{3/2}}$  and  $\text{O}_{1s}$  core levels (Fig. 2c and 2d), no significant discrepancy can be noticed. The  $\text{O}_{1s}$  shapes slightly differ due to the stoichiometry changes of the oxide accordingly to the solvent used and to the water sensitivity of the germanium oxide component of the overall oxide.



**Figure 2:** XPS analysis of the  $\text{Mn}_5\text{Ge}_3$  surface after exposure to acetone and ethanol. a) and b)  $\text{Ge}_{3d}$  core level. c)  $\text{Mn}_{2p_{3/2}}$  and d)  $\text{O}_{1s}$  core levels. (For c) and d), the air exposed case is included as a comparison).

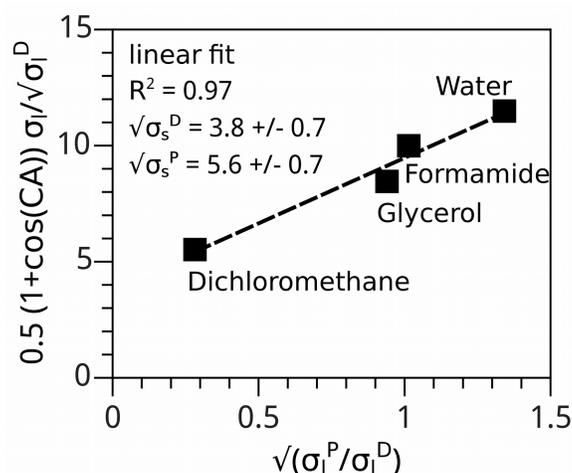
These XPS results clearly show that the oxide layer does not consist only on a germanium oxide layer but contains also a manganese part. Consequently the nature of the oxide layer may be close to that of a ternary oxide Mn-O-Ge. The oxidation state of the  $\text{Mn}_5\text{Ge}_3$  oxide layer slightly changes depending on environmental conditions. This observation was also carried out on Ge surfaces, which are known to exhibit  $\text{Ge}^{2+}$  and/or  $\text{Ge}^{4+}$  oxidation states depending on the surface treatments [31,32].

**3.1.2 Surface free energy (SFE):** SFE determinations have been achieved using the Owens, Wendt, Rabel and Kaelble (OWRK) method with the measure of the contact angles (CAs), with different liquids (deionized water, formamide, glycerol and dichloromethane), on the air exposed  $\text{Mn}_5\text{Ge}_3$

surface [33–35]. Based on the Fowkes' method, the surface free energy is divided into a polar part (non-dispersive, P) and a dispersive part (D) (Eq.1) [36]:

$$\sigma_{sl} = \sigma_s + \sigma_l - 2 \left( \sqrt{\sigma_s^D \sigma_l^D} + \sqrt{\sigma_s^P \sigma_l^P} \right) \quad (\text{Eq.1})$$

The interfacial tension  $\sigma_{sl}$  between liquid and solid is calculated with the two surface tensions  $\sigma_s$  and  $\sigma_l$  of the solid and the liquid and the similar interactions between the phases. These interactions are interpreted as the geometric mean of a dispersive component  $\sigma^D$  and a polar one  $\sigma^P$  of the surface tension. The Figure 3 displays the plot of the OWRK method.

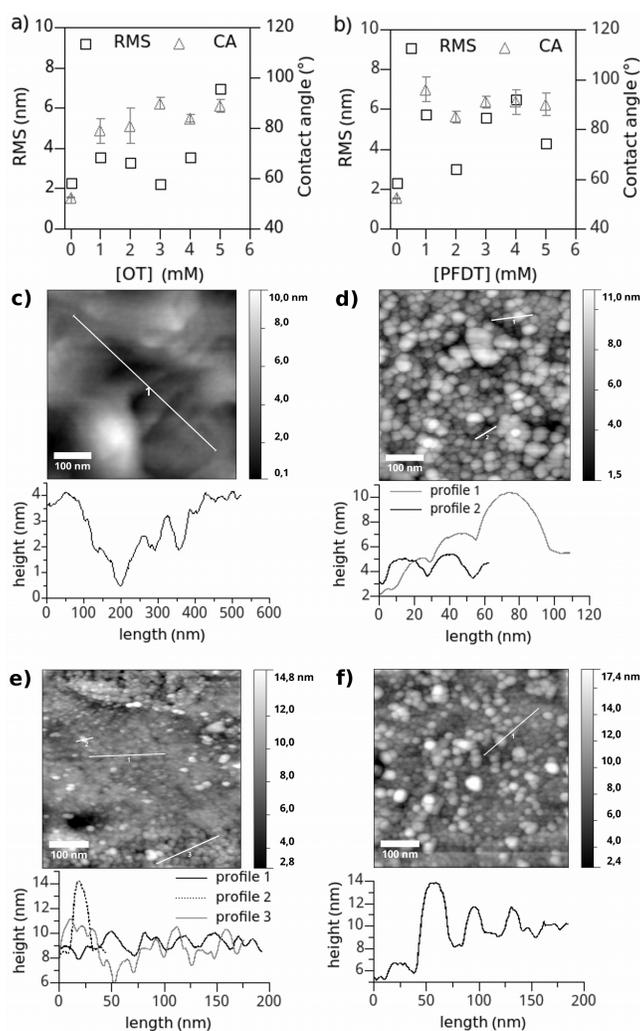


**Figure 3:** Plot of the Owens, Wendt, Rabel and Kaelble method for calculating the surface free energy of the  $\text{Mn}_5\text{Ge}_3$  thin film exposed to air.

The corresponding linear fit affords a dispersive contribution of  $\sigma_{\text{Mn}_5\text{Ge}_3}^D = 14.7 \text{ mJ.m}^{-2}$  and a polar part of  $\sigma_{\text{Mn}_5\text{Ge}_3}^P = 31.8 \text{ mJ.m}^{-2}$ , which corresponds to a total SFE of  $\sigma_{\text{Mn}_5\text{Ge}_3} = 46.5 \text{ mJ.m}^{-2}$ . As for comparison, the SFE of  $\text{SiO}_2$ , an extensively studied surface for SAM deposition, is within the range of  $40\text{--}77 \text{ mJ.m}^{-2}$  with a predominance of the polar component fostering the interactions with polar head-groups such as thiol derivatives [37–39]. In addition, it is known that under vacuum conditions, the surface of  $\text{Mn}_5\text{Ge}_3$  is terminated by Mn atoms therefore the SFE value of an unchanged surface might be close to that of the Mn metal, around  $1350\text{--}1600 \text{ mJ.m}^{-2}$  [40,41]. Moreover, the reported SFE value for a pure manganese oxide surface ( $\text{Mn}_3\text{O}_4$ ,  $72 \text{ mJ.m}^{-2}$ ) supports the XPS data, evidencing that the surface of a  $\text{Mn}_5\text{Ge}_3$  thin film is strongly affected both by air exposition and solvents treatments [42].

### 3.2 Grafting of the $\text{Mn}_5\text{Ge}_3/\text{Ge}(111)$ substrates.

225 The  $\text{Mn}_5\text{Ge}_3/\text{Ge}(111)$  substrates have been subjected to SAMs surface modifications with two different  
alkyl thiols namely OT and PFDT (1-octanethiol and perfluorodecanethiol, respectively) by varying the  
thiol concentrations and then the immersion reaction times. The morphology and wettability of the  
newly formed SAMs were investigated with AFM and water CA measurements, respectively, for a  
given immersion time of 24h. The surfaces roughness obtained from the AFM images and the CA  
230 values are presented on the Figures 4a and 4b (the AFM images are available in the ESI).



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245 **Figure 4:** a)-b) RMS Roughness (from  $2 \times 2 \mu\text{m}^2$  AFM images) and water CA versus thiol molecule concentrations for  $\text{Mn}_5\text{Ge}_3$  surfaces grafted with a) OT and b) PFDT SAMs. (Immersion time = 24h).  
c)-f) AFM images  $500 \times 500 \text{nm}^2$  of OT SAMs for concentration of 0 (image c) (i.e.  $\text{Mn}_5\text{Ge}_3$  bare

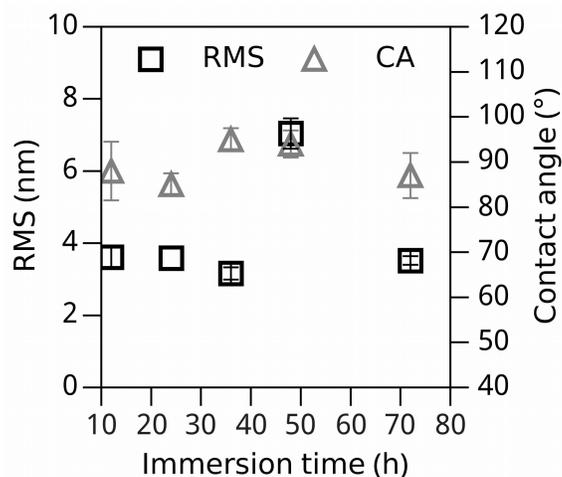
surface), 3 (image d), 4 (image e) to 5 mM (image f) respectively, along with the corresponding profile cross-sections.

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It was observed that OT molecules could easily chemisorb onto the  $Mn_5Ge_3$  surface without any significant changes in the surface roughness, except for concentrations  $\geq 5$  mM. Increasing the solutions concentration ( $\geq 5$  mM) ensue the formation of multilayers that affect dramatically the roughness (fig. 4f). Noteworthy, if the concentration is lower than 4 mM (Figures 4d: 3mM, 4e: 4mM) small separated aggregates of about 30-50 nm in diameter and 2-2,5 nm in height are present within the monolayer. This height is in the range of the length of the grafted molecules ( $\sim 2,5$  nm). A different behaviour was obtained when PFDT was used to passivate the surface of the substrate. Results obtained with PFDT molecules exhibited higher RMS roughness on average but with a greater dispersion of the values. Water CA measurements for each experiment have revealed that the hydrophobicity of the  $Mn_5Ge_3/Ge$  SAM-modified substrate does not significantly change between both thiol molecules regardless the used concentration for an immersion reaction time of 24 hours, reaching values around  $85^\circ$ . However, PFDT molecules provided the highest values of CA at lower concentrations than OT grafting which is normally expected due to higher hydrophobic character of the perfluoroalkyl chains compared to the alkyl chains.

265 In order to evaluate the effect of the immersion time on the  $Mn_5Ge_3/Ge$  functionalization, we have performed the experiments with OT solutions at a concentration of  $[C] = 4$  mM as, both the dispersion of the RMS roughness and the CA values are lower than those measured with the PFDT. The immersion reaction time was varied from 12 to 72 hours. RMS roughness and the water CA are displayed in Figure 5.

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**Figure 5:** RMS roughness and water CA of  $\text{Mn}_5\text{Ge}_3/\text{Ge}$  substrates after functionalization with 4 mM OT as a function of immersion time.

280 No significant difference on the hydrophobicity nor the roughness of the surface was observed by varying the immersion time. The maximum value of the CA was obtained for 36h of immersion and reached  $95^\circ$ , before decreasing slightly. However, the grafting process occurs before 12h of immersion. We observed by AFM (not shown here) that a more homogeneously ordered and dense layer is formed after 36 hours of immersion whereas prolonged immersion time ( $> 48$  hours) conducts to the formation  
285 of aggregates and less ordered layers. This behaviour is similar to the kinetic observed for n-alkylthiolates in 1:1 water-ethanol solvents mixture deposited on Ge surfaces [21,24]. Nevertheless, the measured CAs remain lower than the ones reported on Ge surfaces, around  $100\text{-}110^\circ$ . This feature could be ascribed to an uncompleted coverage of the  $\text{Mn}_5\text{Ge}_3$  surface by the OT SAM or a deterioration of the SAM upon extended immersion time that could facilitate the diffusion of ethanol till the film  
290 surface and leading to a possible dissolution of the oxide layer (attested by a decrease of the CA after 36h).

#### 4 CONCLUSIONS

We presented herein a simple and effective method to deposit SAMs on  $\text{Mn}_5\text{Ge}_3$  thin films. We have  
295 evidenced that thiol derivatives (i.e. OT and PFDT) can easily chemisorb onto  $\text{Mn}_5\text{Ge}_3$  surface as self-assembled monolayers. Our results showed that changes in surface roughness are more pronounced with PFDT than with OT molecules. The optimal conditions, based on the concentrations and immersion reaction time, to ensure well-ordered, dense and homogeneous SAMs were found to be a thiol concentration of  $[C] = 4$  mM and an immersion time of 36 hours. Higher values of these  
300 parameters resulted mainly in an increase of the surface roughness due to the formation of aggregates on the surface and less ordered SAM layers. Comparing the SAMs from OT and PFDT we did not observe any significant changes in the wettability properties of the film surface even it was expected that perfluorinated alkylthiols could render the  $\text{Mn}_5\text{Ge}_3$  surfaces more hydrophobic (C–F bonds are more hydrophobic than the C–H bonds). Further improvements on the deposition methodologies still  
305 need to be matured for  $\text{Mn}_5\text{Ge}_3$  substrate and could lean for instance towards the use of a solvent

mixture of 1:1 ethanol-water and a process temperature around 60-80°C which has been proved to be efficient for the deposition of SAMs onto Ge substrates [21,24]. Moreover, further XPS analysis should be performed on the grafted surfaces so as to assess the formation of the covalent polarized bonds between the molecules and the Mn<sub>5</sub>Ge<sub>3</sub> substrate. Nevertheless this seminal report on functionalization of Mn<sub>5</sub>Ge<sub>3</sub> paves the way to new routes and new opportunities for modifications to access to novel hybrid materials in combination with the fascinating magnetic properties of Mn<sub>5</sub>Ge<sub>3</sub>.

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## Electronic Supplementary Informations (ESI)

### Thiol-functionalization of Mn<sub>5</sub>Ge<sub>3</sub> thin films

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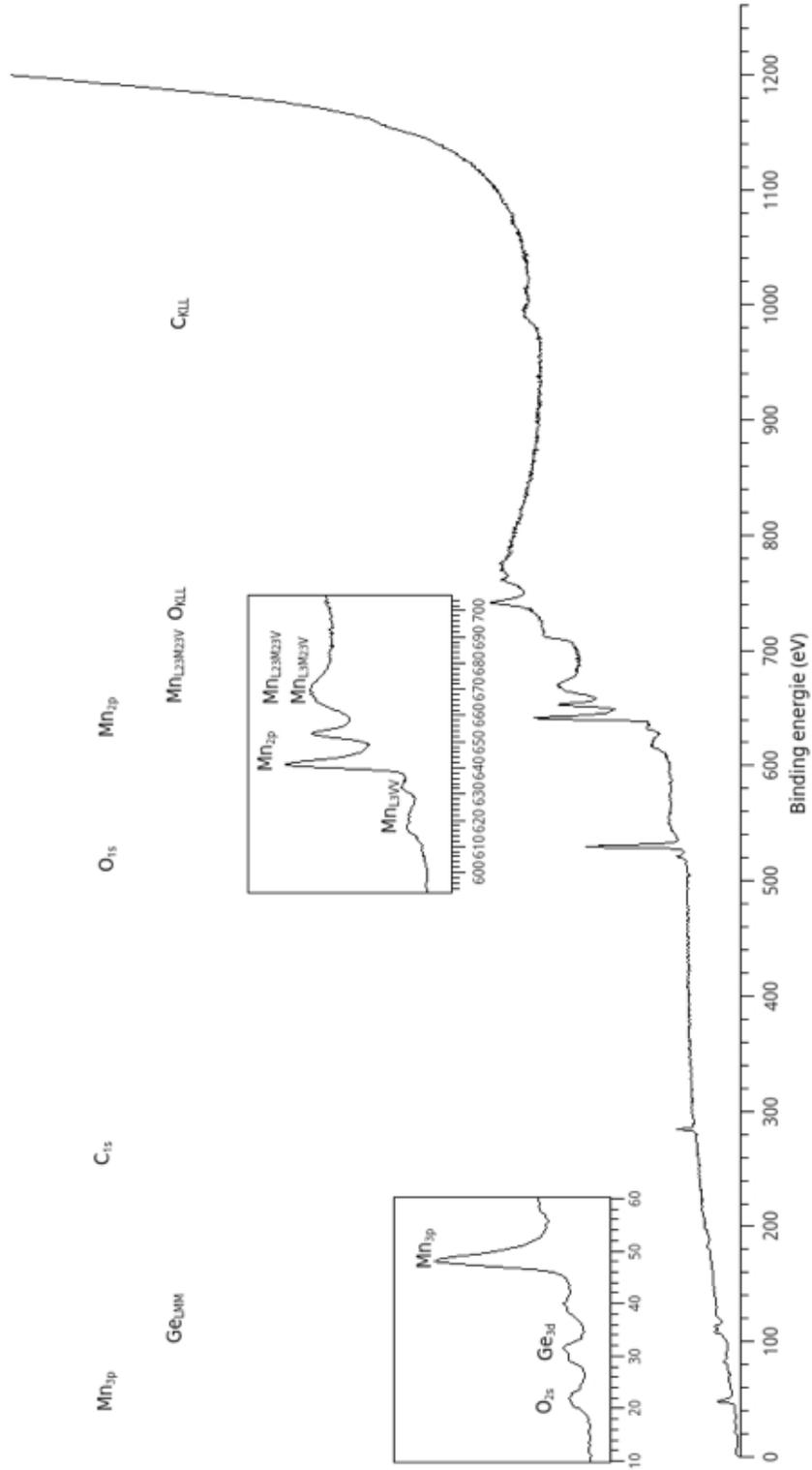
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- 1-** XPS : Survey spectrum of the Mn<sub>5</sub>Ge<sub>3</sub> surface after air exposure **S1**
- 2-** Table related to the fitting parameters used to deconvolute the O<sub>1s</sub> and Ge<sub>3d</sub> core levels (data in eV: accuracy = +/- 1 eV) **S2**
- 3-** Ge<sub>3d</sub> core levels recorded on (left) a cleaned Ge(111) substrate cleaned Mn<sub>5</sub>Ge<sub>3</sub> thin film and (right) an oxidized Ge(111) substrate after air exposure. The Ge<sup>4+</sup> contribution related to the GeO<sub>2</sub> oxide, is prominent **S3**
- 4-** Comparison of the O<sub>1s</sub> core levels of an oxidized Ge(111) substrate and an oxidized Mn<sub>5</sub>Ge<sub>3</sub> thin film after air exposure. **S4**
- 5-** 2x2 μm<sup>2</sup> AFM topography images of Mn<sub>5</sub>Ge<sub>3</sub>/Ge substrate after functionalization with octanethiol (OT) for 24 hours as a function of thiol concentration: a) Mn<sub>5</sub>Ge<sub>3</sub> surface prior to grafting, b)-f) OT concentrations 1, 2, 3, 4, 5 mM. **S5**
- 6-** 2x2 μm<sup>2</sup> AFM topography images of Mn<sub>5</sub>Ge<sub>3</sub>/Ge substrate after functionalization with perfluorodecanethiol (PFDT) for 24 hours as a function of thiol concentration: a)-e) PFDT concentrations 1, 2, 3, 4, 5 mM. **S6**

20 1- XPS: Survey spectrum of the  $Mn_5Ge_3$  surface after air exposure



2- Table related to the fitting parameters used to deconvolute the O<sub>1s</sub> and Ge<sub>3d</sub> core levels (data in  
 25 eV: accuracy = +/- 1 eV):

	After air exposure		After chemical rinsing	
	O <sub>1s</sub>	Ge <sub>3d</sub>	O <sub>1s</sub>	Ge <sub>3d</sub>
FWHM (eV)	1.5	1.1	1.5	1.1
%LG	20	36	20	36
Position of contribution 1 (eV)	529.8	29.1	529.6	29.1
A <sub>1</sub> /A <sub>peak</sub>	0.67	0.43	0.65	0.51
Position of contribution 2 (eV)	531.0	30.9	531.1	30.8
A <sub>2</sub> /A <sub>peak</sub>	0.25	0.20	0.30	0.19
Position of contribution 2 (eV)	532.1	31.7	532.3	31.7
A <sub>3</sub> /A <sub>peak</sub>	0.07	0.37	0.05	0.30

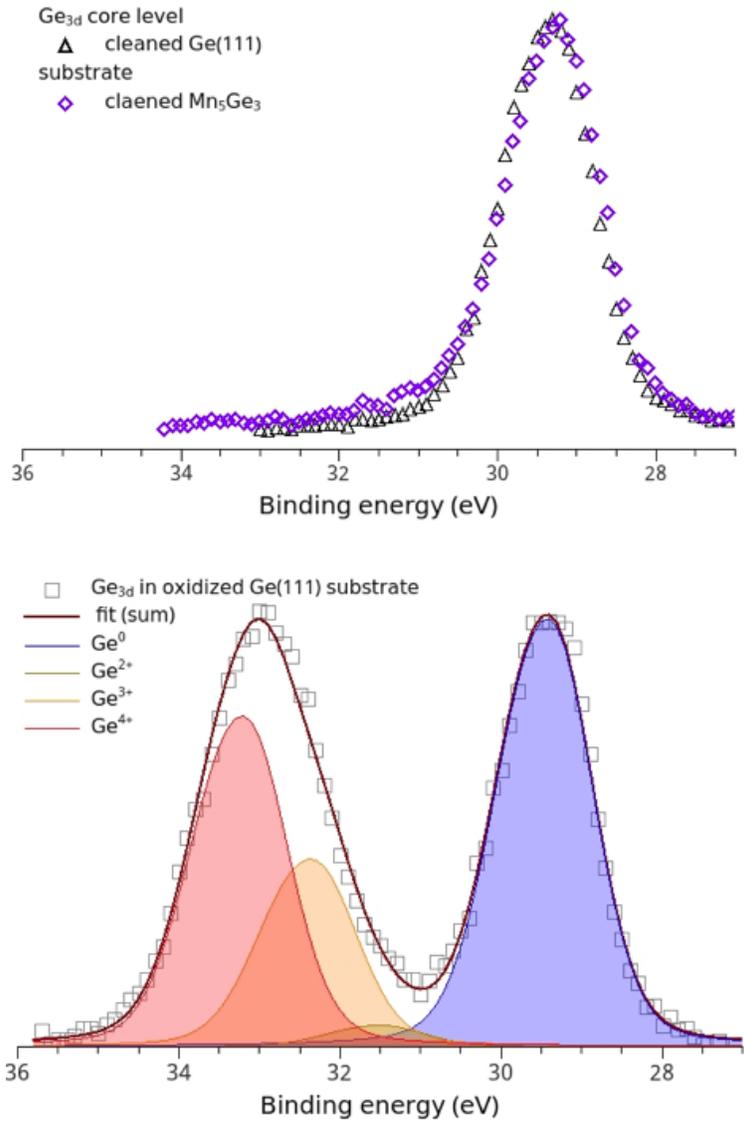
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3-  $\text{Ge}_{3d}$  core levels recorded on (top) a cleaned Ge(111) substrate cleaned  $\text{Mn}_5\text{Ge}_3$  thin film and (bottom) an oxidized Ge(111) substrate after air exposure. The  $\text{Ge}^{4+}$  contribution related to the  $\text{GeO}_2$  oxide, is prominent

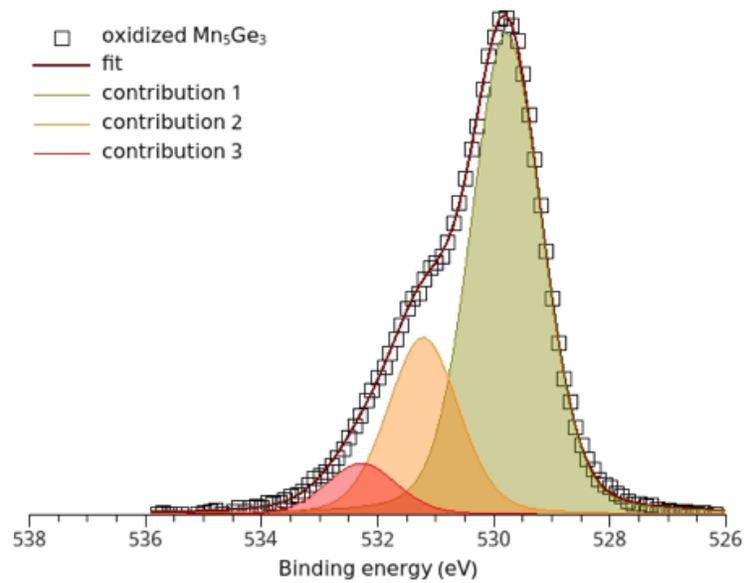
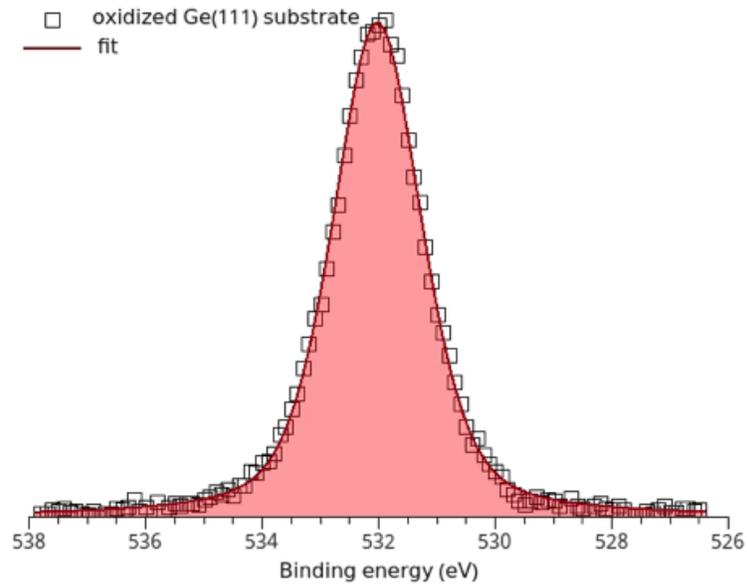


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S3

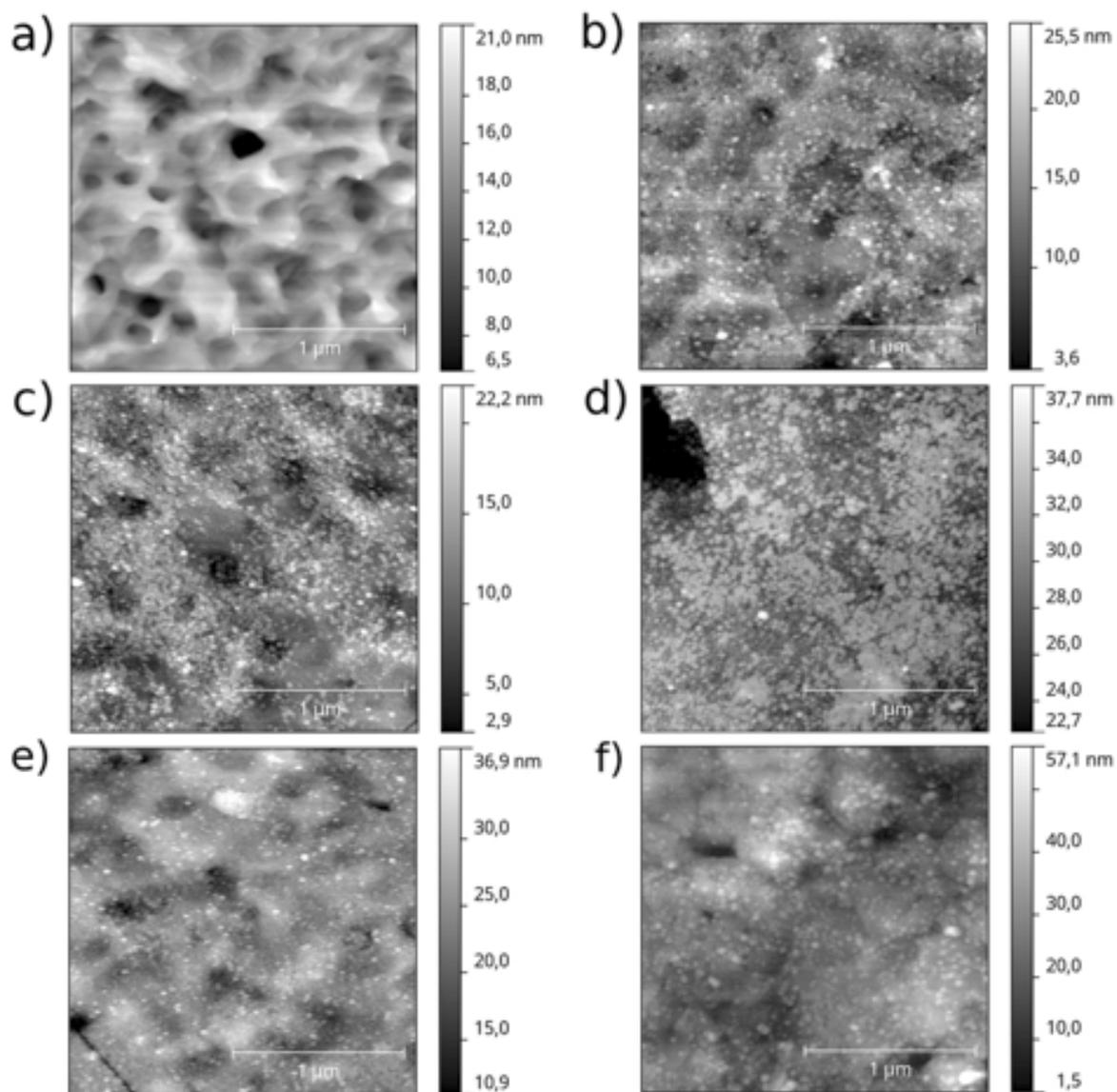
4- Comparison of the  $O_{1s}$  core levels of an oxidized Ge(111) substrate and an oxidized  $Mn_5Ge_3$  thin film after air exposure.



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S4

65 5-  $2 \times 2 \mu\text{m}^2$  AFM topography images of  $\text{Mn}_5\text{Ge}_3/\text{Ge}$  substrate after functionalization with octanethiol (OT) for 24 hours as a function of thiol concentration: a)  $\text{Mn}_5\text{Ge}_3$  surface prior to grafting, b)-f) OT concentrations 1, 2, 3, 4, 5 mM.

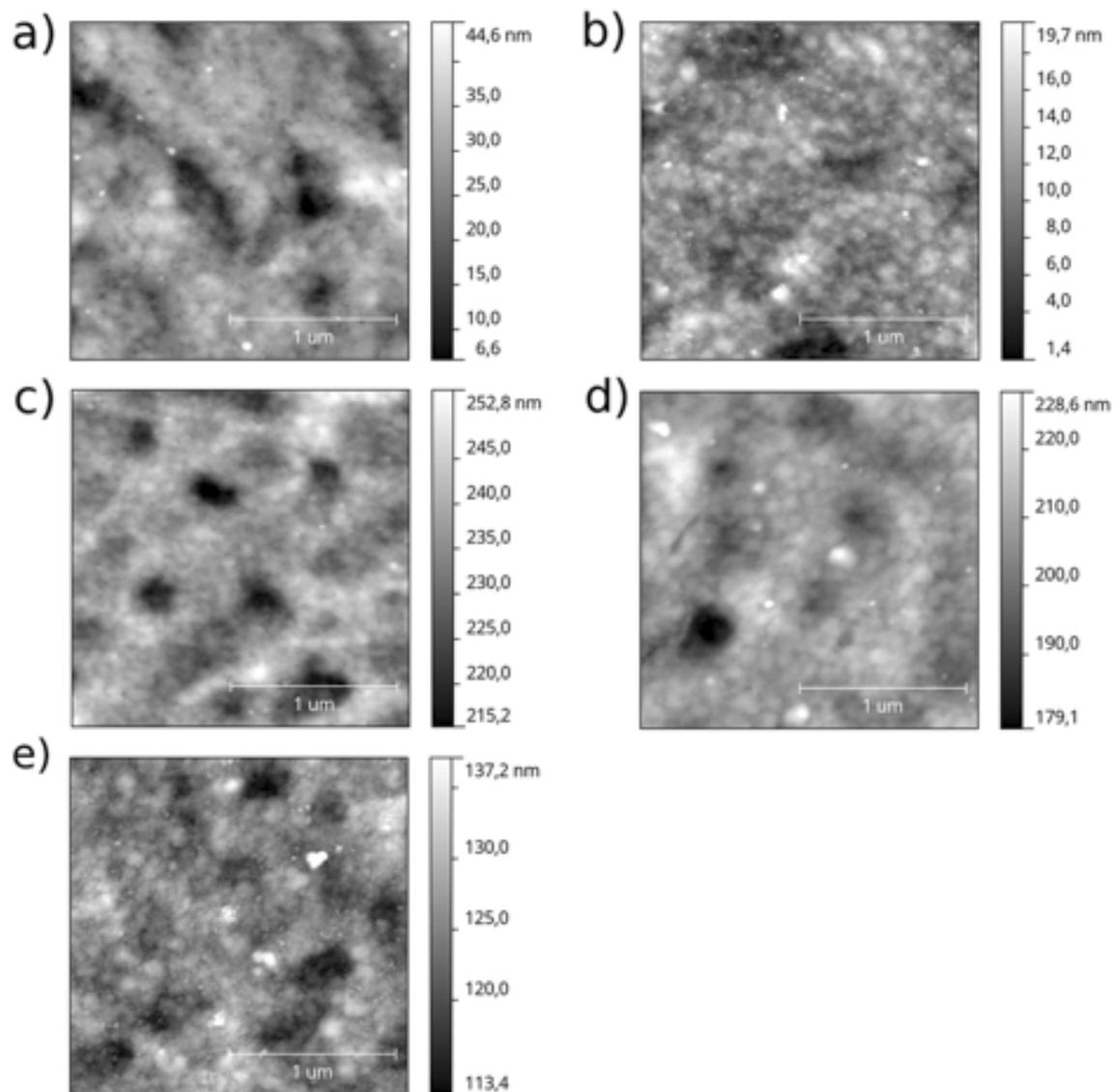


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S5

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6-  $2 \times 2 \mu\text{m}^2$  AFM topography images of  $\text{Mn}_5\text{Ge}_3/\text{Ge}$  substrate after functionalization with perfluorodecanethiol (PFDT) for 24 hours as a function of thiol concentration: a)-e) PFDT concentrations 1, 2, 3, 4, 5 mM.



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